

IGBT MODULE (S series) 600V / 100A / PIM



■ Features

- Low $V_{CE(sat)}$
- Compact package
- P.C. board mount
- Converter diode bridge, Dynamic brake circuit

■ Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

■ Maximum ratings and characteristics

● Absolute maximum ratings ($T_c=25^\circ\text{C}$ unless without specified)

Item	Symbol	Condition	Rating	Unit
Inverter	Collector-Emitter voltage	V_{CES}	600	V
	Gate-Emitter voltage	V_{GES}	± 20	V
	Collector current	I_C Continuous	100	A
		I_{CP} 1ms	200	A
		$-I_C$	100	A
	Collector power dissipation	P_C 1 device	400	W
Brake	Collector-Emitter voltage	V_{CES}	600	V
	Gate-Emitter voltage	V_{GES}	± 20	V
	Collector current	I_C Continuous	50	A
		I_{CP} 1ms	100	A
	Collector power dissipation	P_C 1 device	200	W
Converter	Repetitive peak reverse voltage	V_{RRM}	600	V
	Repetitive peak reverse voltage	V_{RRM}	800	V
	Average output current	I_O 50Hz/60Hz sine wave	100	A
	Surge current (Non-Repetitive)	I_{FSM} $T_j=150^\circ\text{C}$, 10ms	700	A
	I^2t (Non-Repetitive)	I^2t half sine wave	2450	A^2s
	Operating junction temperature	T_j	+150	$^\circ\text{C}$
	Storage temperature	T_{stg}	-40 to +125	$^\circ\text{C}$
	Isolation between terminal and copper base *2	AC : 1 minute	AC 2500	V
	voltage between thermistor and others *3		AC 2500	V
	Mounting screw torque		3.5 *1	N·m

*1 Recommendable value : 2.5 to 3.5 N·m (M5)

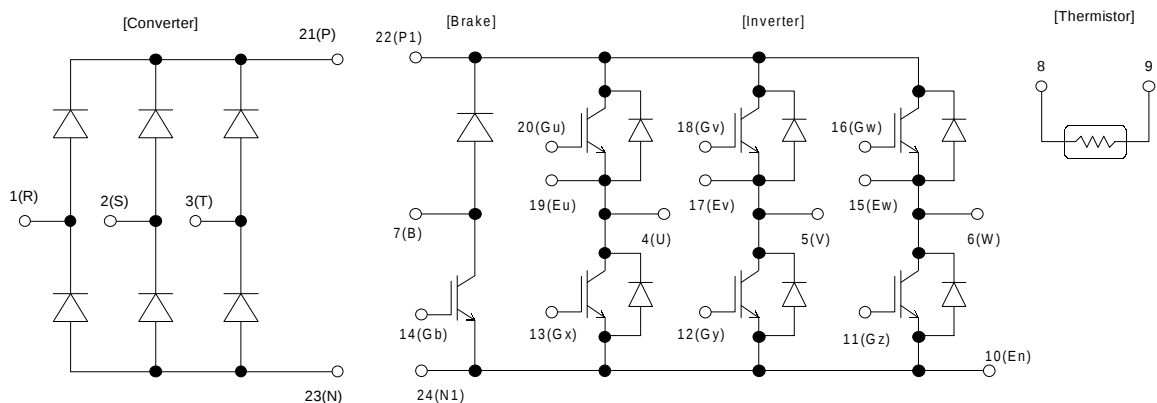
*2 All terminals should be connected together when isolation test will be done.

*3 Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 24 should be connected together and shorted to copper base.

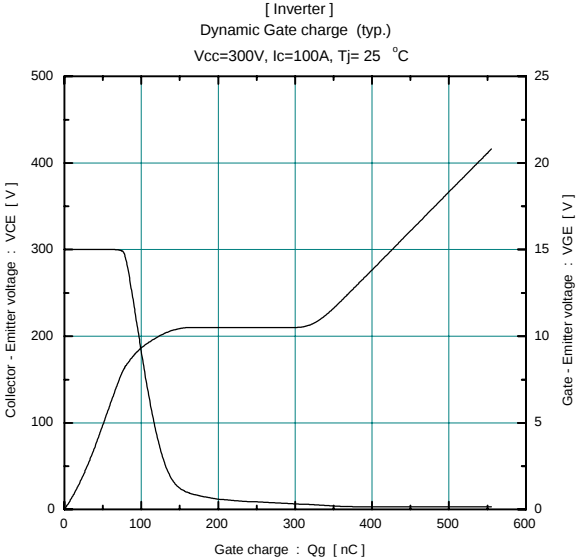
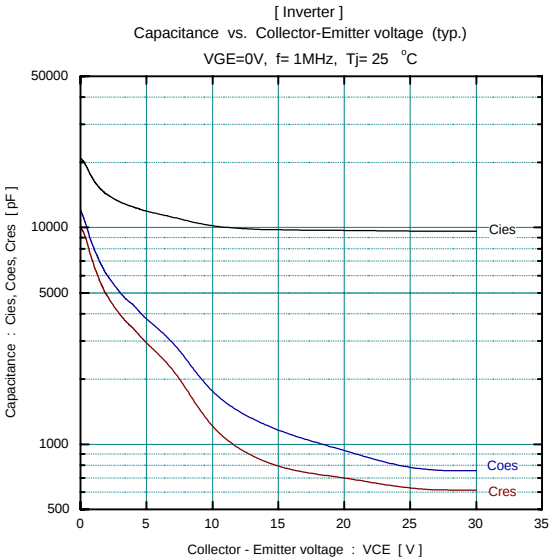
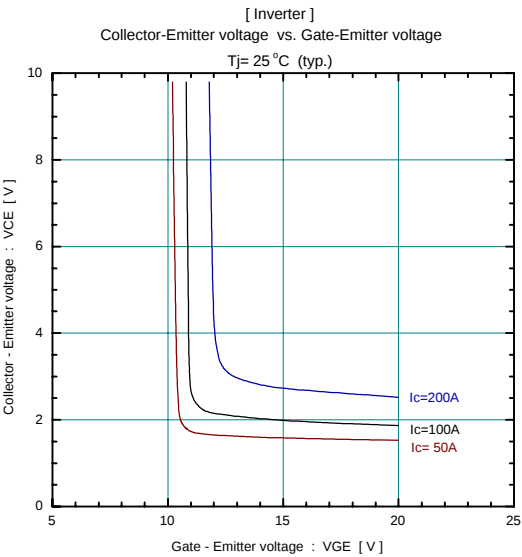
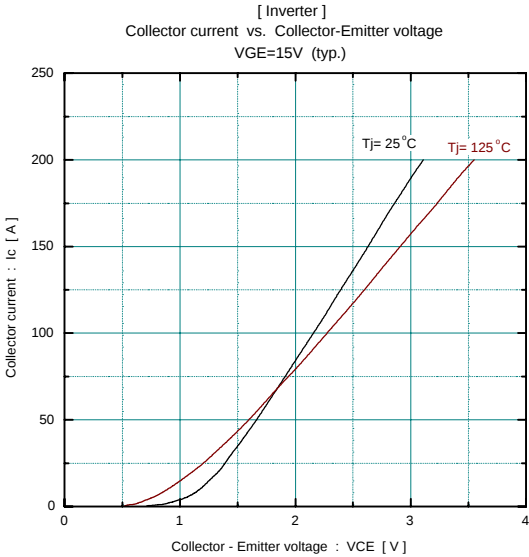
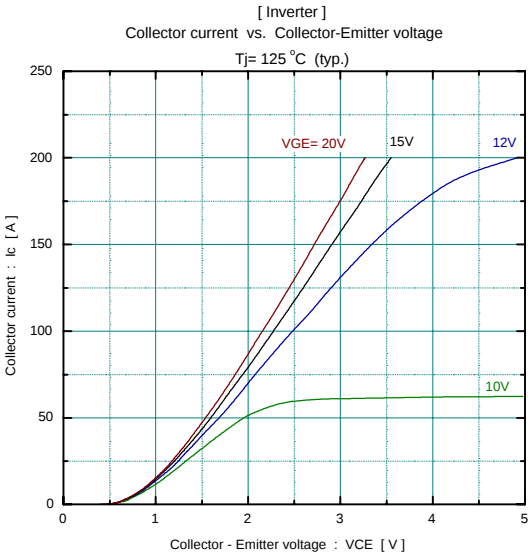
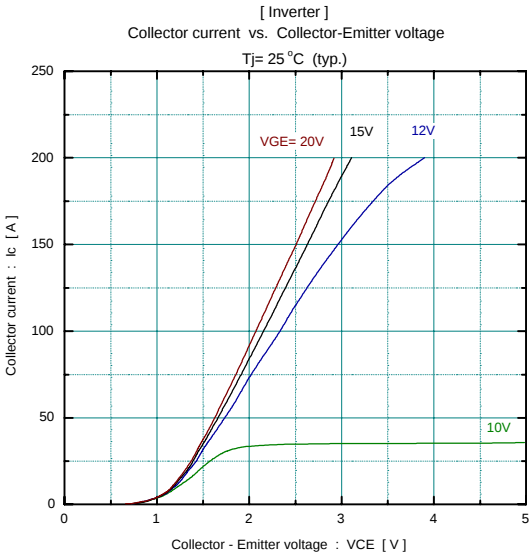
Item		Symbol	Condition		Characteristics			Unit
					Min.	Typ.	Max.	
Inverter	Zero gate voltage collector current	ICES	VCE=600V, VGE=0V				1.0	mA
	Gate-Emitter leakage current	IGES	VCE=0V, VGE=±20V				0.2	µA
	Gate-Emitter threshold voltage	VGE(th)	VCE=20V, IC=100mA		5.5	7.8	8.5	V
	Collector-Emitter saturation voltage	VCE(sat)	VGE=15V, IC=100A	chip		1.8		V
				terminal		2.15	2.6	
	Input capacitance	Cies	VGE=0V, VCE=10V, f=1MHz			10000		pF
	Turn-on time	ton	VCC=300V			0.45	1.2	µs
		tr	IC=100A			0.25	0.6	
		tr(i)	VGE=±15V			0.08		
	Turn-off	toff	RG=24Ω			0.40	1.0	
		tf				0.05	0.35	
	Forward on voltage	VF	IF=100A	chip		1.6		V
				terminal		1.95	2.7	
	Reverse recovery time of FRD	trr	IF=100A				0.3	µs
Brake	Zero gate voltage collector current	ICES	VCES=600V, VGE=0V				1.0	mA
	Gate-Emitter leakage current	IGES	VCE=0V, VGE=±20V				0.2	µA
	Collector-Emitter saturation voltage	VCE(sat)	IC=50A, VGE=15V	chip		1.8		V
				terminal		2.05	2.5	
	Turn-on time	ton	VCC=300V			0.45	1.2	µs
		tr	IC=50A			0.25	0.6	
	Turn-off time	toff	VGE=±15V			0.40	1.0	
		tf	RG=51Ω			0.05	0.35	
Converter	Reverse current	IRRM	VR=600V				1.0	mA
	Forward on voltage	VFM	IF=100A	chip		1.1		V
				terminal		1.2	1.5	
	Reverse current	IRRM	VR=800V				1.0	mA
Thermistor	Resistance	R	T=25°C			5000		Ω
			T=100°C		465	495	520	
	B value	B	T=25/50°C		3305	3375	3450	K

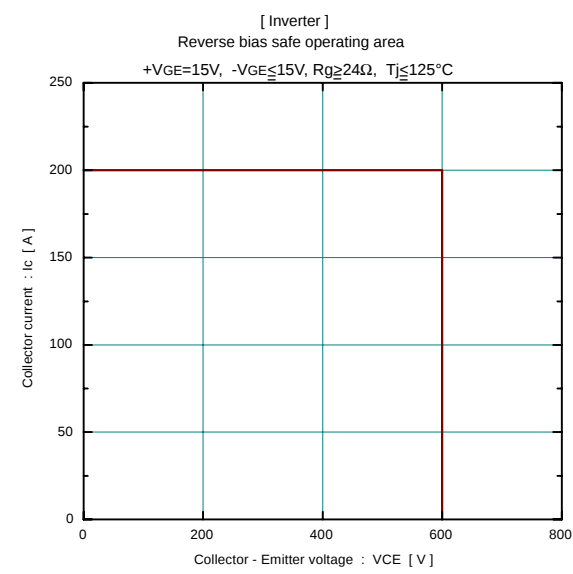
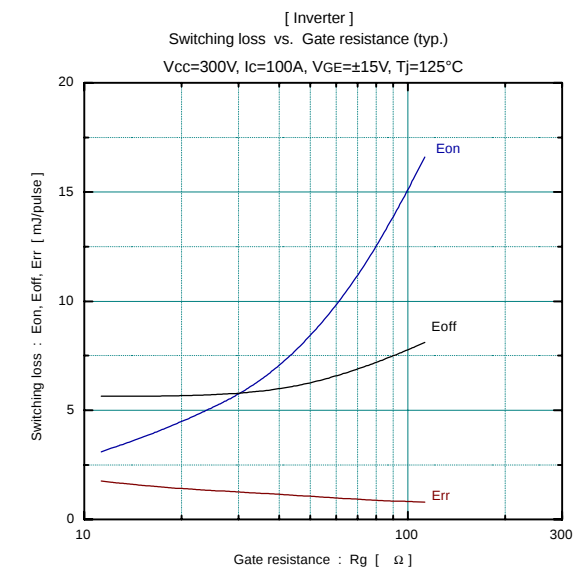
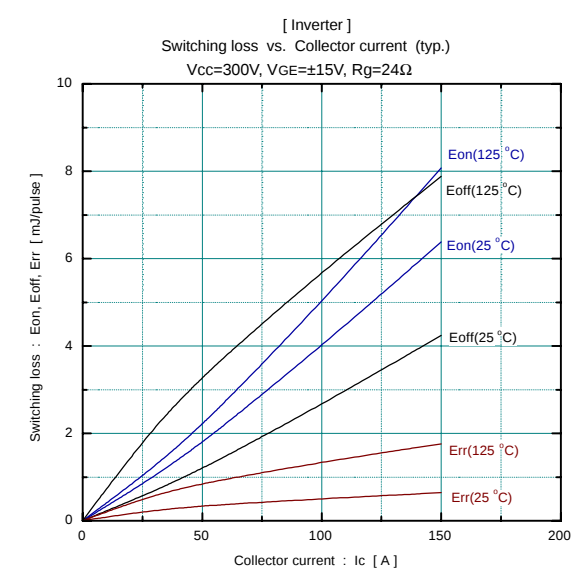
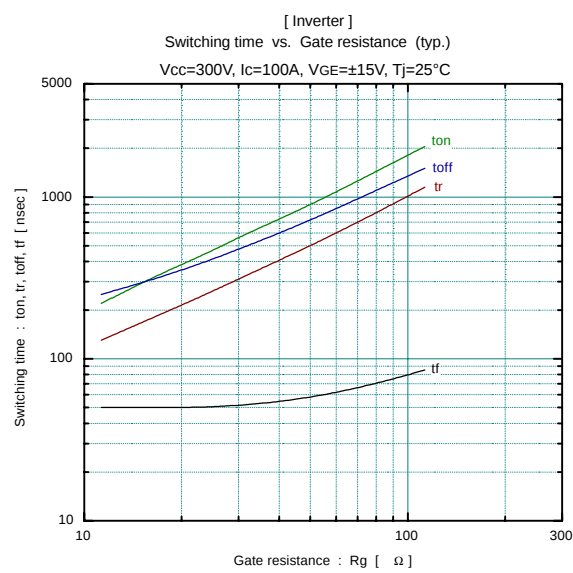
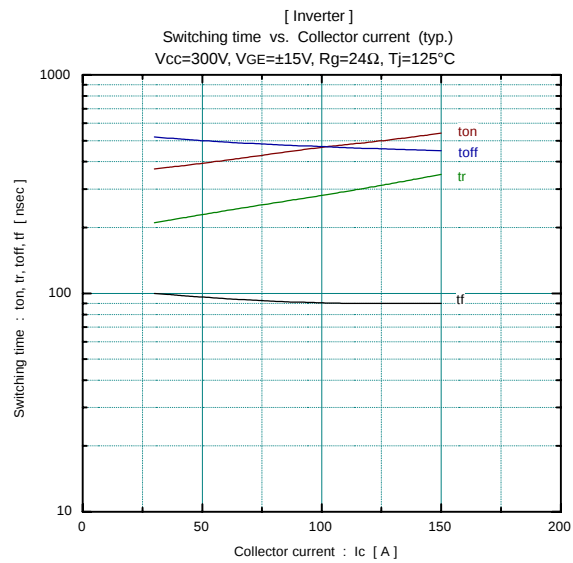
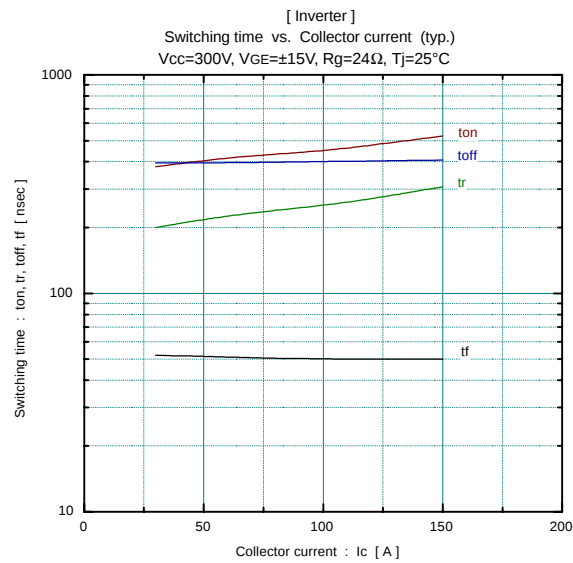
Item	Symbol	Condition	Characteristics			Unit
			Min.	Typ.	Max.	
Thermal resistance (1 device)	Rth(j-c)	Inverter IGBT			0.31	°C/W
		Inverter FWD			0.70	
		Brake IGBT			0.63	
		Converter Diode			0.47	
Contact thermal resistance *	Rth(c-f)	With thermal compound		0.05		

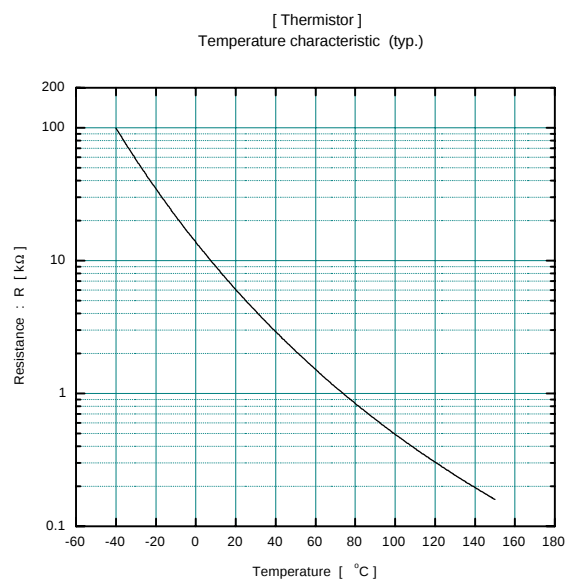
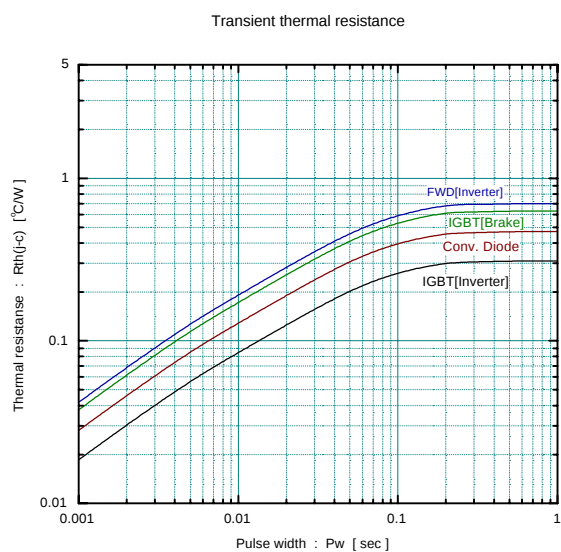
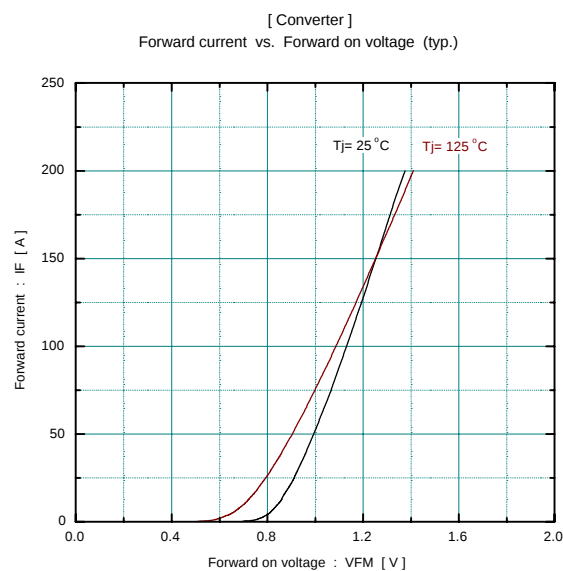
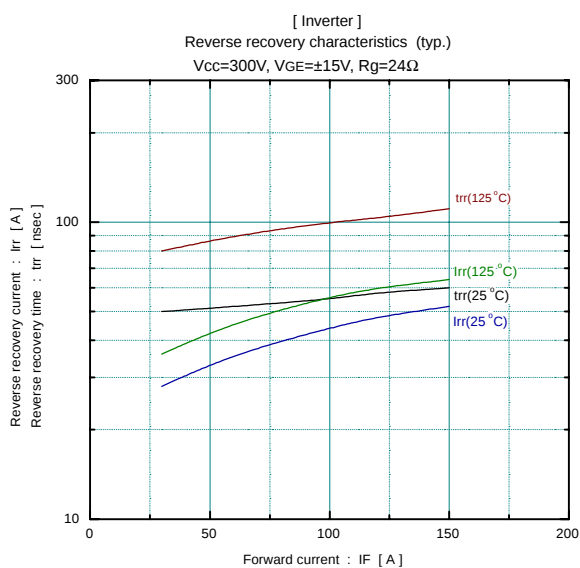
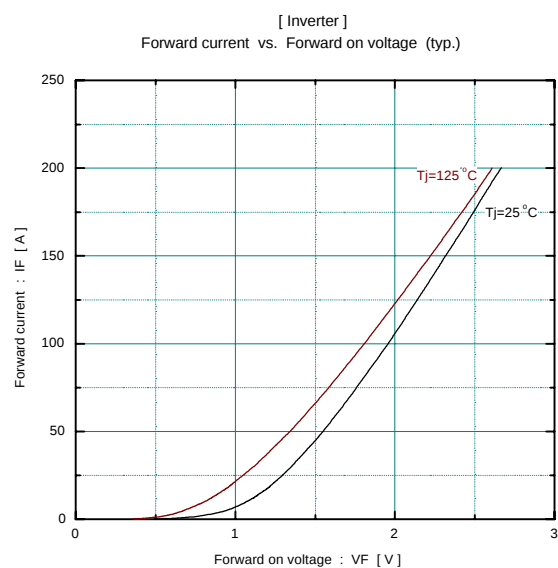
■ Equivalent Circuit Schematic

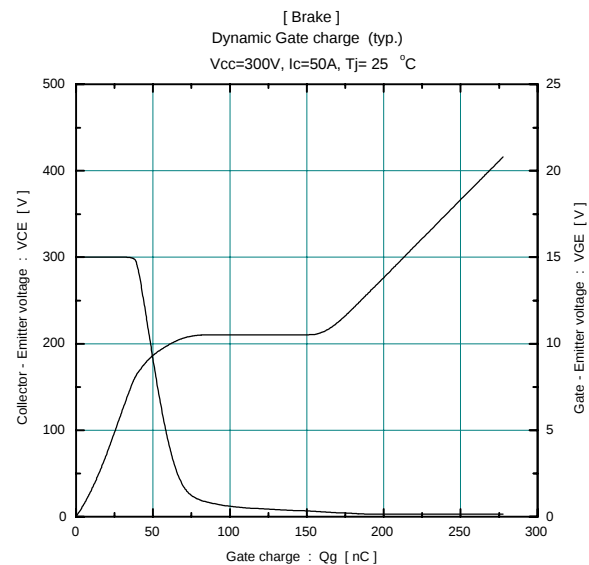
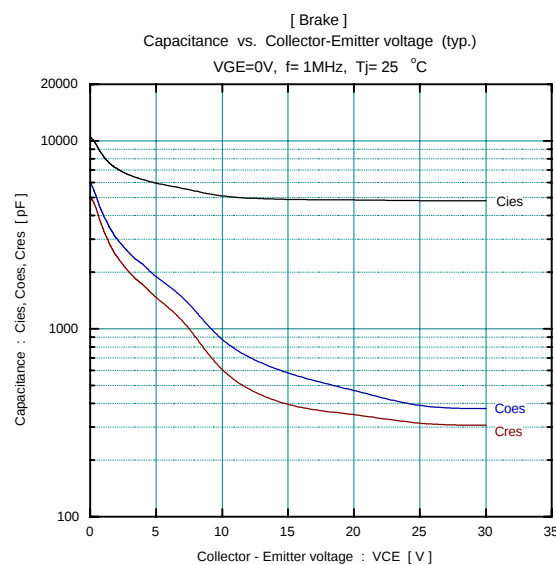
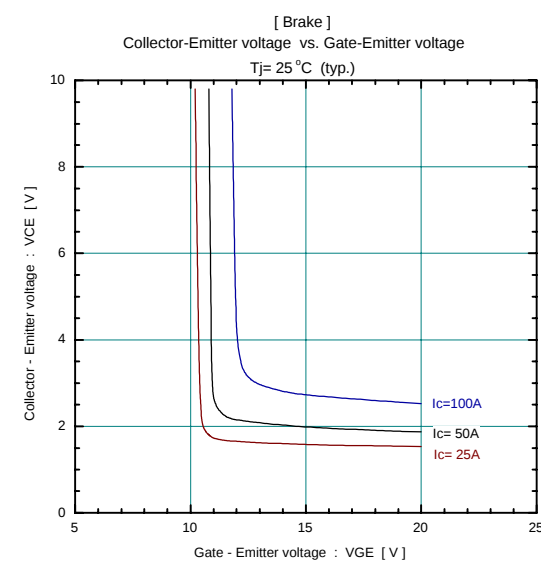
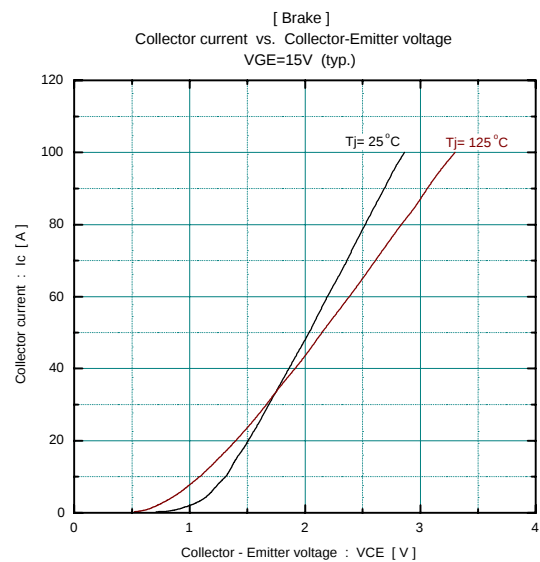
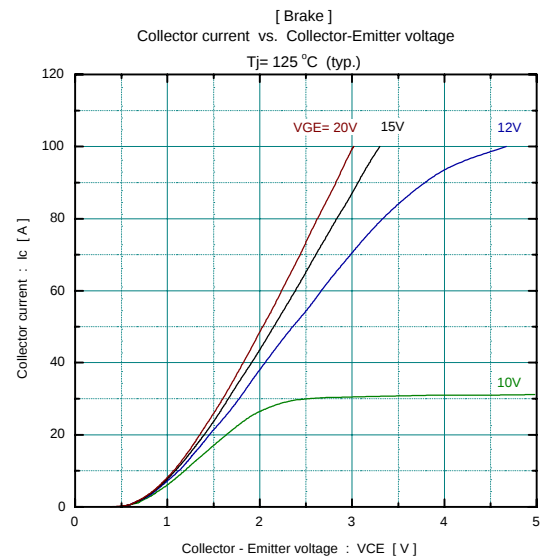
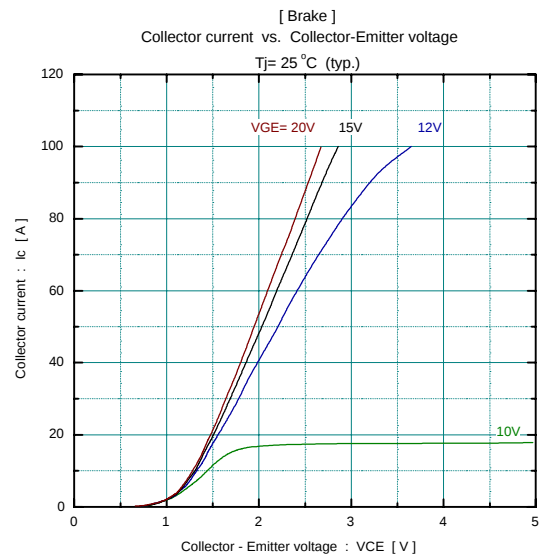


■ Characteristics (Representative)

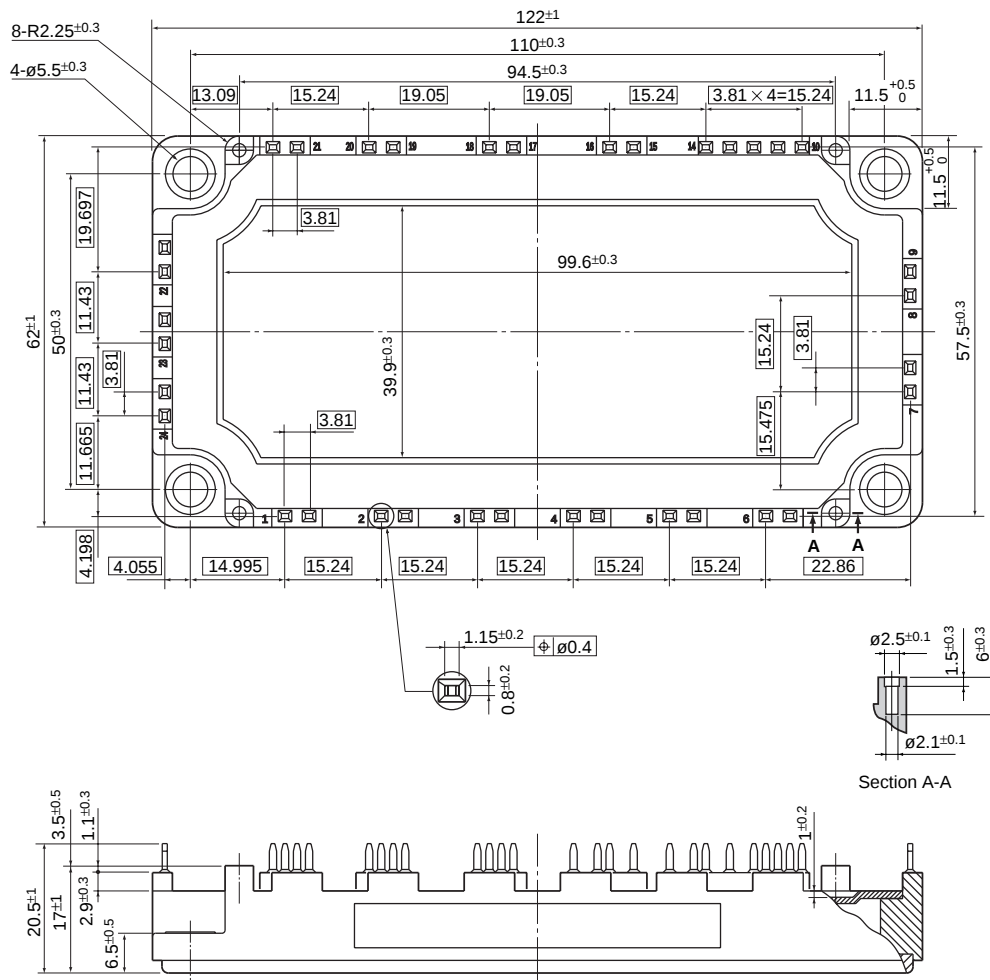








■ Outline Drawings, mm



☐ Shows theory dimensions